This GIDEP PCN is to announce specifications change with the datasheet parameters for the following International Rectifier Part No. Note that this change is related to part specification only, and not due to a die physical change.

IRFF130 [2N6796]
100V, N-Channel Hi-Rel MOSFET in a TO-205AF package

ELECTRICAL CHARACTERISTICS @ Tj = 25°C
R_{DS(on)} \text{[Static Drain-to-Source On-State Resistance]}, change max limit from 207mΩ to 195mΩ.
Q_g \text{[Total Gate Charge]}, change max limit from 28.5nC to 28.51nC.
Q_{gs} \text{[Gate-to-Source Charge]}, change max limit from 6.3nC to 6.34nC.
Q_{gd} \text{[Gate-to-Drain (‘Miller’) Charge]}, change max limit from 16.6nC to 16.59nC.
Remove Gate Charge minimum limits.

Reference Datasheet PD-90430